

V1.0 Datasheet

N-Channel 40V MOSFET

FEATURES

- ●Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

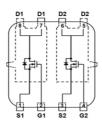
PRODUCTY SUMMARY					
V_{DS}	$R_{DS(on)} m(\Omega)$ Max				
40	9.4	@V _{GS} =10V			
40	12.4	@V _{GS} =4.5V			

Application

- ●Portable Devices
- ■Consumer Electronics

DFN5060





Mechanical

●Case:DFN5060 Package

Packing Information

Package	Packing		
DFN5060	3Kpcs/13"Reel		

Maximum Ratings (T _A =25°C unless otherwise specified)							
Parameter	Symbol	Limit	Unit				
DrainSource Voltage	V _{DS}	40	V				
GateSource Voltage	V _{GS}	±20	V				
Continuous Drain Current 1)	I _{DSM}	20	А				
Continuous Drain Current 4)	I _D	80	А				
Continuous Drain Current 5)	I _{DM}	144	А				
Maximum Power Dissipation	P _D	6	W				
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C				

Typical Thermal Resistance						
Parameter Symbol Limit						
JunctiontoAmbient Thermal Resistance 3)		34	°C/W			

Note:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Fused current that based on wire numbers and diameter.
- 3. Guaranteed by design, not subject to production testing.
- 4. The maximum current rating is package limited.
- 5. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keepinitial T_J =25°C.



Electrical Characteristics (T _A = 25°C UNLESS OTHERWISE NOTED)						
Characteristics	Symbol	Test Condition	Limits			l lm:t
Characteristics			Min	Тур	Max	Unit
Static						
DrainSource Breakdown Voltage	B _{VDSS}	V_{GS} =0V, I_D =250uA	40	-	-	V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250uA$	1.00	1.40	3.00	V
DrainSource OnState Resistance	R _{DS(on)}	V_{GS} =10V, I_{D} =20.0A	-	8.0	9.4	mΩ
DrainSource OnState Resistance		V_{GS} =4.5V, I_{D} =20.0A	-	10.5	12.4	mΩ
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	1	uA
GateSource Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA

DrainSource Diode						
Maximum Continuous Body Diode Forward Current	Is	-	-	-	1.2	А
Diode Forward Voltage	V_{SD}	I _S =1.0A, V _{GS} =0V	-	-	1.5	V

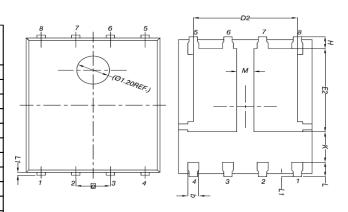
Note:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- $5.\ R_{QJA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch2 with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.



Package Outline Dimensions (inches and millimeters)

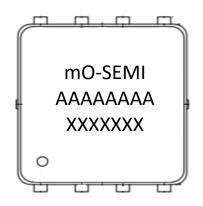
DFN5060							
	Dimensions						
SYMBOL	Millir	neters	Inch	ies			
	Min	Max	Min	Max			
Α	0.90	1.10	0.035	0.043			
b	0.33	0.51	0.013	0.020			
С	0.20	0.30	0.008	0.012			
D1	4.80	5.00	0.189	0.197			
D2	3.61	3.96	0.142	0.156			
E	5.90	6.10	0.232	0.240			
E1	5.70	5.80	0.224	0.228			
E2	3.38	3.78	0.133	0.149			
е	1.27bsc						
Н	0.41	0.61	0.016	0.024			
K	1.100	-	0.043	-			
L	0.51	0.71	0.020	0.028			
L1	0.06	0.20	0.002	0.008			
М	0.50	-	0.020	-			
α	0 °	12 °	-	-			







Marking Information



First line = Company name

AAAAAAA = Product number

XXXXXXX = Tracking number

Fourth line = Pin1 Point

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